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## FET (Field Effect Transistors) MCQ Test

### Take FET (Field Effect Transistors) MCQ Test & Online Quiz to test your Knowledge

Below is the **FET (Field Effect Transistors) MCQ** test that checks your basic knowledge of FET (Field Effect Transistors). This **FET (Field Effect Transistors) MCQ Test** contains 20 Multiple Choice Questions. You have to select the right answer to the question. Finally, you can also take the Online Quiz from the **Take FET (Field Effect Transistors) Quiz** Button.

**Q1. What do you know about field-effect transistor (FET)?**

- **A. a type of transistor which uses an electric field to control the flow of current**
- B. voltage
- C. Current
- D. None of the above

**Q2. FET acts as constant current source in \_\_\_\_.**

- **A. Ohmic region**
- B. Breakdown region
- C. Pinch off region
- D. All of the above

**Q3. Which of the following is the common features between FETs and bipolars?**

- A. Difficult to bias
- B. Low voltage gain
- C. Low input impedance
- **D. Current controlled devices**

**Q4. Is FETs are preferred to BJTs at high frequencies because they are less noisy?**

- **A. Yes**

- B. No

**Q5. FETs are preferred to BJTs at high frequencies because they are \_\_\_\_.**

- **A. less noisy**
- B. capable of handling highest frequencies
- C. easy to fabricate
- D. All of the above

**Q6. A JFET has three terminals, namely \_\_\_\_.**

- A. cathode, anode, grid
- B. emitter, base, collector
- **C. source, gate, drain**
- D. None of the above

**Q7. The gate of a JFET is \_\_\_\_ biased.**

- **A. reverse**
- B. forward
- C. reverse as well as forward
- D. None of the above

**Q8. In saturation region JFET acts like a \_\_\_\_.**

- A. Switch
- B. Short circuit
- C. Bipolar device
- **D. Resistance**

**Q9. The input impedance of an ideal JFET \_\_\_\_.**

- A. is impossible to predict
- B. approaches unity
- **C. approaches infinity**
- D. approaches zero

**Q10. The name field effect is related to the \_\_\_\_ layers of a JFET.**

- **A. depletion**
- B. gate
- C. source
- D. drain

**Q11. MOSFET is a three-terminal device with gate (G), drain (D) and source (S) terminals.**

- **A. True**
- B. False

**Q12. Which of the following devices has the highest input impedance?**

- A. JFET
- **B. MOSFET**
- C. Crystal diode
- D. ordinary transistor

**Q13. A MOSFET uses the electric field of a \_\_\_\_ to control the channel current.**

- **A. capacitor**
- B. battery
- C. generator
- D. All of the above

**Q14. What is the full form of MOSFET?**

- **A. metal–oxide–semiconductor field-effect transistor**
- B. metal–oxygen–semiconductor field-effect transistor
- C. metal–oxide–semi field-effect transistor
- D. All of the above

**Q15. The source terminal of a JEFT corresponds to cathode of a vacuum tube.**

- **A. True**

- B. False

**Q16. The type of bias most often used with E-MOSFET circuits is \_\_\_\_.**

- A. constant current
- **B. drain-feedback**
- C. voltage-divider
- D. zero biasing

**Q17. The operation of a JFET involves a flow of \_\_\_\_.**

- A. Recombination carriers
- **B. Majority carriers**
- C. Minority carriers
- D. All of the above

**Q18. A FET differs from a bipolar transistor as it has \_\_\_\_.**

- A. simpler fabrication
- B. negative resistance
- **C. high input impedance**
- D. All of the above

**Q19. N-channel FETs are superior to P-channel FETs because \_\_\_\_.**

- A. these have a higher switching
- B. these have a higher input impedance
- **C. mobility of electron is greater than that of holes**
- D. All of the above

**Q20. A FET can be used as a variable \_\_\_\_.**

- A. Inductor
- B. Capacitor
- **C. Voltage source**
- D. Current source